

Silicon NPN Power Transistors

2SC2266

**DESCRIPTION**

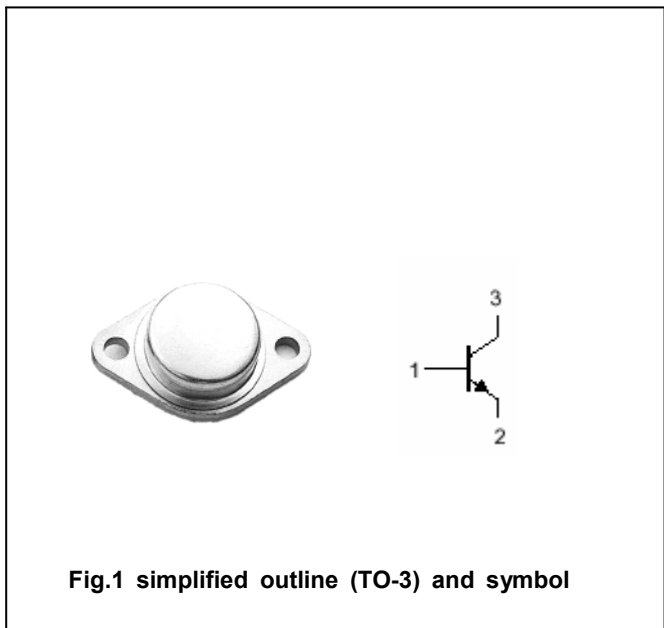
- With TO-3 package
- High dielectric strength
- Short switching time

**APPLICATIONS**

- For switching regulator application

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**MAXIMUM RATINGS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	500	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		10	A
$I_B$	Base current		3	A
$P_T$	Total power dissipation	$T_{mb} \leq 25^\circ C$	100	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-65~150	$^\circ C$

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th j-c}$	Thermal resistance from junction to case	1.25	$^\circ C/W$

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	400			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =1.6A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =8A; I <sub>B</sub> =1.6A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =400V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1.6A ; V <sub>CE</sub> =5V	10		50	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =8A ; V <sub>CE</sub> =5V	8			

PACKAGE OUTLINE

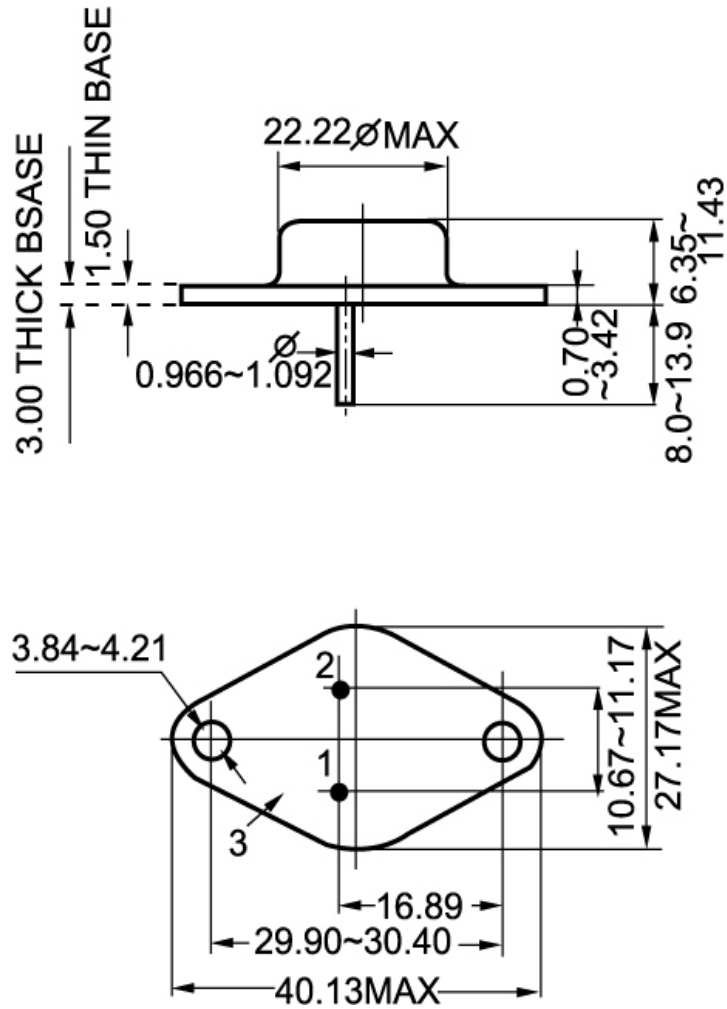


Fig.2 Outline dimensions